

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2651	pulse near5 deposit\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:36
L2	463	1 and (silicon near5 oxide)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:37
L3	0	2 and (phosphorous near5 dop\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 17:29
L4	72	2 and phosphorus	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 17:31
L5	9625	(cycle pulse) near5 deposit\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 17:31
L6	1548	5 and (silicon near5 oxide)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 17:31
L7	297	6 and phosphorus	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 17:32
L8	265	7 and semiconductor	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:23
L9	140	8 and (phosphorus near5 dop\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:33
L10	421	pulse near20 (CVD (chemical near3 vapor near3 deposit\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:34
L11	945	(pulse cycle) near20 (CVD (chemical near3 vapor near3 deposit\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:34
L12	454	11 and (silicon near5 (oxide dioxide))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:35
L13	8	12 and (phosphorus near20 dop\$3 near20 (silicon near5 (oxide dioxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:36
L14	693	pulse near5 deposit\$3	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/17 18:37
L15	630	1 and (silicon near5 (oxide dioxide))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 18:37

L16	8	14 and (silicon near5 (oxide dioxide))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 18:37
-----	---	----------------------------------------	--------------------------------------	----	----	---------------------

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	34898	ALD (atomic near5 layer near5 deposit\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:20
L2	33	1 and (phosphorus near5 (silicon near5 (oxide dioxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 11:42
L3	33	2 and phosphorus	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 11:30
L4	1490	ALD (atomic near5 layer near5 deposit\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:42
L5	0	4 and (phosphorus near5 (silicon near5 (oxide dioxide)))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:43
L6	1	4 and (phosphorus and (silicon and (oxide dioxide)))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:44
L7	4496	PSG (phosphours near5 doped near5 (silicon near5 (dioxide oxide)))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:47
L8	4496	PSG (phosphours near5 dop\$3 near5 (silicon near5 (dioxide oxide)))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:47
L9	4496	7 8	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:46
L10	0	9 and (ALD (atomic near5 layer near5 deposit\$3))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/03/17 11:46
L11	12679	PSG (phosphours near5 doped near5 (silicon near5 (dioxide oxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 11:47
L12	12679	PSG (phosphours near5 dop\$3 near5 (silicon near5 (dioxide oxide)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 11:47
L13	12679	11 12	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 11:47

L14	261	13 and (ALD (atomic near5 layer near5 deposit\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:19
L15	178	("Si" near3 "OR" near3 "OH")	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:20
L16	627	("PO" near3 "OR")	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:20
L17	9	15 and 16	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:21
L18	0	17 and (ALD (atomic near5 layer near5 deposit\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:20
L19	796	15 16	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:21
L20	72	19 and (silicon near5 (oxide dioxide))	US-PGPU B; USPAT; USOCR	OR	ON	2005/03/17 12:22